



60V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
60V	16mΩ @ V _{GS} = 10V	31.8A
	$22m\Omega$ @ V _{GS} = 4.5V	27.6A

Features

- 100% Unclamped Inductive Switching (UIS) Test in Production— Ensures More Reliable and Robust End Application
- Low On-Resistance
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Wettable Flank for Improved Optical Inspection
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance (RDS(ON)) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- Backlighting
- Power Management Functions
- DC-DC Converters

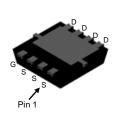
Mechanical Data

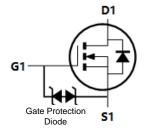
- Case: PowerDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish—Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (23)
- Weight: 0.072 grams (Approximate)

PowerDI3333-8 (SWP) (Type UX)









Top View

Bottom View

Equivalent Circuit

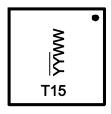
Ordering Information (Note 4)

Part Number	Case	Packaging
DMT6015LFVW-7	PowerDI3333-8 (SWP) (Type UX)	2000/Tape & Reel
DMT6015LFVW-13	PowerDI3333-8 (SWP) (Type UX)	3000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



T15 = Product Type Marking Code

YYWW = Date Code Marking

YY = Last Two Digits of Year (ex: 20 = 2020)

WW = Week Code (01 to 53)



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	VDSS	60	V		
Gate-Source Voltage	V _{GSS}	±16	V		
Continuous Drain Current, $V_{GS} = 10V$ (Note 6) $T_{C} = +25^{\circ}C$ $T_{C} = +70^{\circ}C$			lσ	31.8 25.5	А
Continuous Drain Current, V _{GS} = 10V (Note 5) Steady State		T _A = +25°C T _A = +70°C	I _D	10.0 8.0	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	127	Α		
Maximum Continuous Body Diode Forward Current (Not	Is	31.8	Α		
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)		Isм	127	Α	
Avalanche Current, L = 0.1mH			I _{AS}	20.7	Α
Avalanche Energy, L = 0.1mH			Eas	21.4	mJ

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

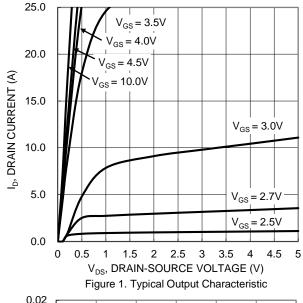
Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	$T_A = +25$ °C	P_{D}	2.8	W
Thermal Resistance, Junction to Ambient (Note 5) Steady State		$R_{\theta JA}$	44.2	°C/W
Total Power Dissipation (Note 6)	PD	28.4	W	
Thermal Resistance, Junction to Case (Note 6)	$R_{ heta JC}$	4.4	°C/W	
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C	

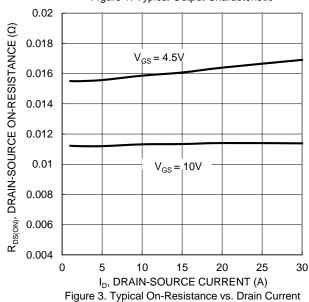
Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

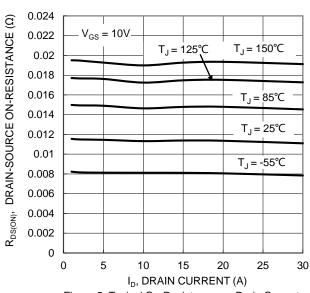
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage		60	_	_	V	$V_{GS} = 0V$, $I_{D} = 250 \mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 48V, V_{GS} = 0V$	
Gate-Source Leakage	Igss	_	_	±10	μΑ	$V_{GS} = \pm 16V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	Vgs(TH)	1.2	_	2.5	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	D	_	11.3	16	mΩ	Vgs = 10V, ID = 10A	
Static Dialit-Source Off-Resistance	RDS(ON)	_	15.8	22	mΩ	$V_{GS} = 4.5V, I_D = 6A$	
Diode Forward Voltage	VsD	_	0.7	1.2	V	V _G S = 0V, I _S = 1A	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss	_	808	_	pF	, 20V V 0V	
Output Capacitance	Coss	_	279	_	pF	V _{DS} = 30V, V _{GS} = 0V, f = 1MHz	
Reverse Transfer Capacitance	C _{rss}	_	30	_	pF		
Gate Resistance	Rg	_	1.4	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (VGS = 4.5V)	Qg	_	8.6	_	nC		
Total Gate Charge (VGS = 10V)	Qg	_	15.7	_	nC	\/ 20\/ I- 40A	
Gate-Source Charge	Qgs	_	2.9	_	nC	V _{DS} = 30V, I _D = 10A	
Gate-Drain Charge	Qgd	_	3.4	_	nC	1	
Turn-On Delay Time	tD(ON)	_	7.5	_	ns	$V_{DD} = 30V, V_{GS} = 10V,$ $R_g = 6\Omega, I_D = 10A$	
Turn-On Rise Time	t _R	_	2.7	_	ns		
Turn-Off Delay Time	t _{D(OFF)}	_	17.4	_	ns		
Turn-Off Fall Time	tF	_	8.9	_	ns		
Body Diode Reverse Recovery Time	t _{RR}	_	26.7	_	ns	104 11/11 1004/	
Body Diode Reverse Recovery Charge	Q _{RR}	_	16.2	_	nC	I _F = 10A, di/dt = 100A/μs	

Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 Thermal resistance from junction to soldering point (on the exposed drain pad).
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.



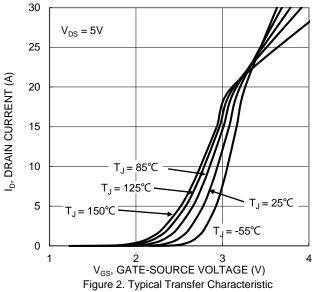


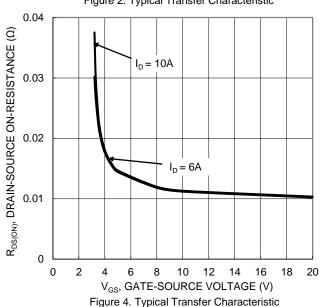




and Gate Voltage

Figure 5. Typical On-Resistance vs. Drain Current and Temperature





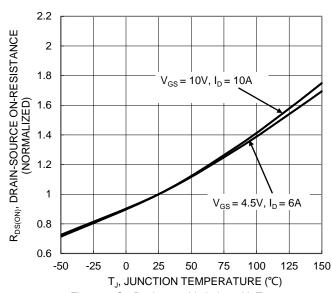
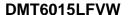


Figure 6. On-Resistance Variation with Temperature





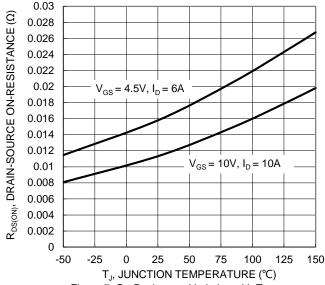
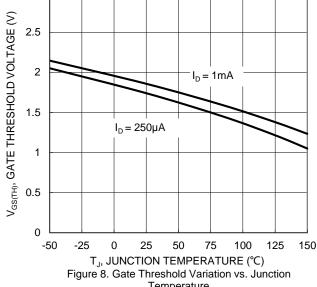


Figure 7. On-Resistance Variation with Temperature



3

Temperature

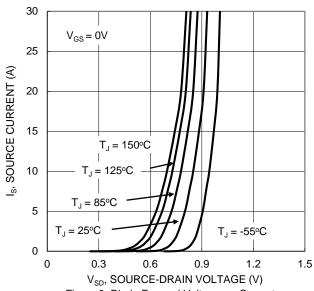
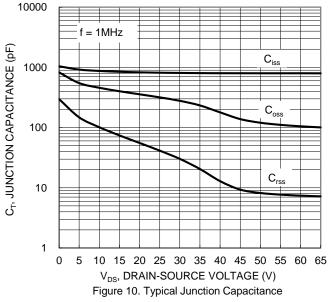
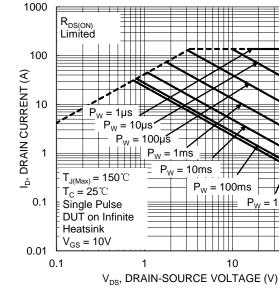


Figure 9. Diode Forward Voltage vs. Current





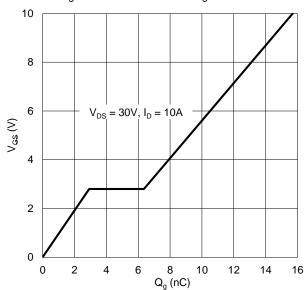


Figure 11. Gate Charge

Figure 12. SOA, Safe Operation Area

 $P_W = 10ms$

P_W = 100ms

100



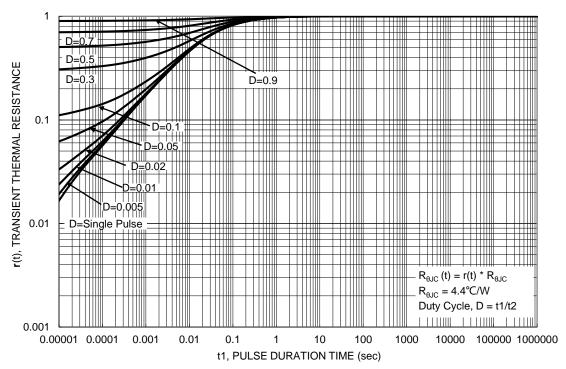


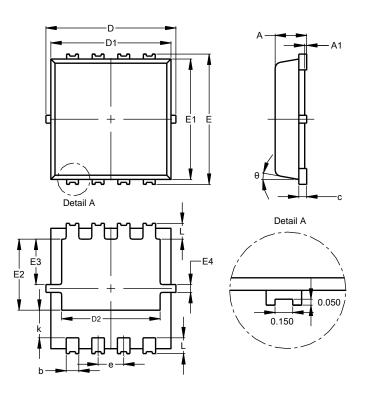
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

 $\label{prop:package-outlines.html} Please see \ http://www.diodes.com/package-outlines.html \ for \ the \ latest \ version.$

PowerDI3333-8 (SWP) (Type UX)

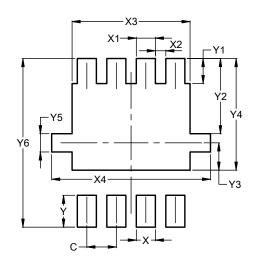


PowerDI3333-8 (SWP)					
(Type UX)					
Dim	Min Max Ty		Тур		
Α	0.75	0.85	0.80		
A1	0.00	0.05			
b	0.25	0.40	0.32		
С	0.10	0.25	0.15		
D	3.20	3.40	3.30		
D1	2.95	3.15	3.05		
D2	2.30	2.70	2.50		
Е	3.20	3.40	3.30		
E1	2.95	3.15	3.05		
E2	1.60	2.00	1.80		
E3	0.95	1.35	1.15		
E4	0.10	0.30	0.20		
е	_	_	0.65		
k	0.50	0.90	0.70		
L	0.30	0.50	0.40		
θ	0°	12°	10°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)



Dimensions	value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
Х3	2.600
X4	3.500
Y	0.700
Y1	0.550
Y2	1.650
Y3	0.600
Y4	2.450
Y5	0.400
Y6	3.700



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